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# MgB<sub>2</sub> thick films on three-dimensional structures fabricated by HPCVD

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#### **Abstract**

Magnetic shielding has been a key factor in the measurement of ultra-weak magnetic fields, especially for shielding from low frequency electromagnetic noise. With the recent development of superconducting quantum interference devices, superconducting magnetic shielding has become an important area of research. MgB<sub>2</sub> has shown great potential in magnetic shielding for its remarkable superconducting properties, the feasibility of its use in this capacity having been demonstrated by MgB<sub>2</sub> bulk samples. However, the potential for application of such bulk samples is limited. In this work, we have investigated the possibility of the fabrication of MgB<sub>2</sub> films on three-dimensional (3D) structures using a hybrid physical—chemical vapor deposition system. MgB<sub>2</sub> films 10  $\mu$ m thick have been fabricated on the outer surface of a polycrystalline Al<sub>2</sub>O<sub>3</sub> cylinder. The deposited film showed a transition temperature (T<sub>C</sub>) of 39 K and J<sub>C</sub> of 5.1 × 10<sup>5</sup> A · cm<sup>-2</sup>, which are comparable to those of planar MgB<sub>2</sub> films. This work shows the feasibility of depositing MgB<sub>2</sub> films onto a 3D structure, and sheds light on the potential use of MgB<sub>2</sub> films in superconducting magnetic shielding.

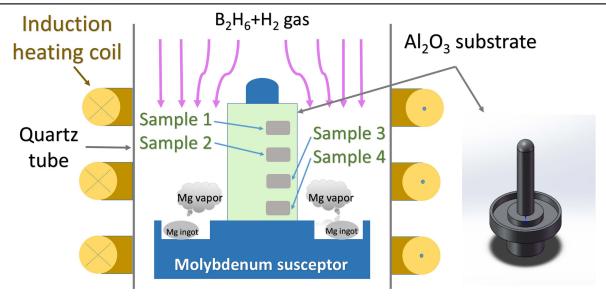
Keywords: magnesium diboride, thick film deposition, HPCVD

(Some figures may appear in colour only in the online journal)

## 1. Introduction

The binary intermetallic compound MgB<sub>2</sub> has attracted great interest in both fundamental studies and practical applications since its superconductivity was discovered in 2001 [1]. Due to its remarkable superconducting properties, such as high superconducting transition temperature (T<sub>C</sub>) of 39 K [2], simple crystalline structure, high critical current density  $(J_C)$ [3], and absence of weak links at grain boundaries [4], MgB<sub>2</sub> is considered to be one of the most promising superconducting materials for such applications as mediumstrength superconducting magnets [5], Josephson junction devices [6], and digital circuits [7]. Various forms of MgB<sub>2</sub>, such as films, tapes, polycrystalline wires, micro whiskers, etc, have been fabricated in the past few decades [8-12]. Among these, MgB2 films are highly valued because of their outstanding performance and flexibility in practical application.

A variety of methods have been developed to fabricate MgB<sub>2</sub> films, including pulsed laser deposition [13], molecular beam epitaxy (MBE) [14], electron beam evaporation [15], and hybrid physical-chemical vapor deposition (HPCVD) [3]. Among these techniques, HPCVD seems to be the most effective way to fabricate high-performance MgB<sub>2</sub> films from several nanometers to dozens of micrometers thick [3, 16-20]. Most of the research on HPCVD has focused on planar surfaces, as planar MgB2 films can be used in many applications like kinetic inductance detectors [21], superconducting quantum interference devices (SQUIDs) [5], and hot-electron bolometer mixers [22], etc. However, in some cases, non-planar MgB2 films are needed-such as superconducting radio frequency (SRF) cavities [23, 24], magnetic shielding tubes [5], etc, where MgB<sub>2</sub> films are required to be fabricated on three-dimensional (3D) structures. In our previous work, the experiment of fabricating MgB<sub>2</sub> planar films on stainless steel and then bending it to a certain angle has been conducted. Cracks between films and substrate arose



**Figure 1.** Schematic of the modified HPCVD system. The image to the right is a 3D depiction of the molybdenum susceptor. The hollow  $Al_2O_3$  cylindrical substrate is set on a molybdenum cylinder.

with increasing bend angle, which degraded the performance of superconducting films [25]. Therefore, the study of techniques to fabricate such films on three-dimensional structures is needed.

Anti-electromagnetic interference plays an important role in the measurement of ultra-weak magnetic signals, especially for low frequency interference. For example, the most sensitive magnetic detector SQUID usually needs to be put in a magnetic shielding tube to obtain high resolution for magnetic fields. Superconducting magnetic shielding (SMS) has an outstanding shielding effect against both high and low frequency interference. Low temperature SMS has been successfully developed using niobium, and Nd<sub>3</sub>Sn and has been widely used, while SMS above liquid helium temperature is still unavailable. As a medium temperature superconducting material, MgB2 is a material of interest for high temperature SMS [26]. The magnetic shielding capability of MgB<sub>2</sub> has previously been verified using MgB2 bulk cylinders [5, 27, 28], but the dimensions and geometric shapes of magnetic shielding tubes for which this form can be used are limited. Three-dimensional MgB2 films can maintain the magnetic shielding capability while meeting the dimension and outline demands of a range of technical needs, whence they have great research value. Very recently, Xi et al tried to fabricate MgB<sub>2</sub> films directly inside a Cu tube to meet the demand of SRF cavities, and got promising results [29, 30]; the T<sub>C</sub> is in the range of 30–38 K, which indicates that HPCVD can be used in 3D film fabrication. For magnetic shielding, non-metal tubes with thick MgB<sub>2</sub> films are required. Films fabricated on non-metal 3D structure need to be studied.

In this work, we report the fabrication of MgB<sub>2</sub> thick films on a cylindrical structure of polycrystalline  $Al_2O_3$  by HPCVD. High-performance MgB<sub>2</sub> films of  $10 \,\mu m$  thickness were obtained. The  $T_C$  values of the films were above 39 K, comparable with those of planar films fabricated by HPCVD.

Microstructure and conducting performance of the film have been studied.

## 2. Experiments

The detailed setup of HPCVD has been described in previous articles [31]. A modified HPCVD system was built to fabricate MgB2 thick films on the outside surfaces of 3D structures. The schematic diagram of the HPCVD system is shown in figure 1. The growth of MgB<sub>2</sub> films during HPCVD is sensitive to the annealing temperature. To make sure the outer surface of the 3D structure had a uniform temperature distribution, an induction heating apparatus was used as the heating source, replacing the conventional resistive coil. A quartz tube instead of a stainless steel cylinder was assembled as a reactor chamber so that induction heating on the sample could be easily controlled. In this work, thick MgB2 films were deposited on the outer surfaces of polycrystalline Al<sub>2</sub>O<sub>3</sub> hollow cylinders (the outside diameter being 18 mm and inner diameter 12 mm). A specially designed molybdenum susceptor (figure 1) was used as a sample holder and inductive heating source. The Al<sub>2</sub>O<sub>3</sub> hollow cylindrical substrate was set on the molybdenum cylinder. Mg ingots (99.5% in purity) with masses of 3-4 g were placed on the susceptor as the Mg source. A gas mixture of 25% diborane (B<sub>2</sub>H<sub>6</sub>) and 75% hydrogen was used as the boron source.

During MgB<sub>2</sub> film growth, ultra-high purity hydrogen gas (99.9999%) was introduced into the chamber as ambient gas at a flow rate of 300 sccm and a pressure of 5 kPa, to provide a reducing reaction environment. Next, the substrate and solid Mg ingots along with the susceptor were heated up inductively to the set temperature of 610 °C. When the Mg ingots started to melt at  $\sim$ 550 °C, mixed B<sub>2</sub>H<sub>6</sub> gas was introduced at the flow rate of 10 sccm into the reactor. The temperature was then fixed at 610 °C for 15 min with the

**Table 1.** Positions (distinguished by vertical distance from the susceptor) and thickness of the samples.

	Sample 1	Sample 2	Sample 3	Sample 4
Position (mm)	2.5	7.5	12.5	17.5
Thickness (μm)	8.9	9.9	11.2	

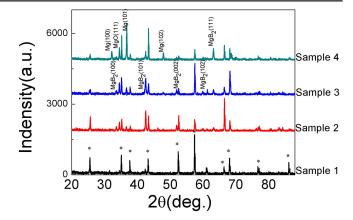
pressure stabilized at around 6 kPa.  $B_2H_6$  met the Mg vapor at the induction heating region and reacted to form MgB<sub>2</sub> which was deposited on the surface of the cylindrical substrate. Finally, the fabricated films were cooled down to room temperature in flowing  $H_2$  gas.

The thickness of each sample was measured using a stylus profiler (AlphaStep D-500) after chemically etching a step on the films. The phase purity and crystallinity were analyzed using a Philp X'pert x-ray diffractometer (XRD). The surface micromorphology of the MgB<sub>2</sub> films were characterized using a scanning electron microscope (FEI NOVA Nano-SEM 430). The temperature-dependent resistance ( $\rho$ -T curve) was carried out using the standard four-probe method. The critical current densities  $J_{\rm C}$  were calculated using the Bean model from the magnetization hysteresis loops (M-H curve) obtained from a Quantum Design Magnetic Property Measurement System (MPMS-7).

## 3. Results and discussion

To study the variation of the superconducting property of the film with changes in position, four small sample pieces were cut out from different regions (figure 1) and distinguished by the vertical distance from the susceptor, as shown in table 1. Note that thicker films were deposited on the lower samples, where higher Mg vapor pressure can be expected. The average thicknesses measured were as shown in table 1 except for Sample 4, the thickness of which could not be measured specifically. Dendritic Mg deposition was found on top of Sample 4, which created large errors in thickness measurements. As for the other samples, the thickness increased slightly as the distance from the bottom of the susceptor decreased. From samples 2 and 3, at the optimum deposition position, an average thickness of  $10 \,\mu m$  was measured. A deposition rate of 11.1 nm s<sup>-1</sup> can be calculated, which is higher than that of conventional HPCVD [3, 16-18]. The deposition rate is determined by the pressure of Mg vapor and the flow rate of B<sub>2</sub>H<sub>6</sub>. The variation of the thickness of the film at the same height is less than 1  $\mu$ m.

The crystalline structure of the films was explored by XRD, and is shown in figure 2. From Sample 1 to Sample 3, the intensity of Al<sub>2</sub>O<sub>3</sub> peak gradually decreased while the intensity of MgB<sub>2</sub> peaks increased, which indicates that the MgB<sub>2</sub> film had a polycrystalline structure and became denser and thicker as it was placed lower and closer to the Mg source. Impurities of Mg and MgO can also be noticed in the MgB<sub>2</sub> films, which were mainly caused by the re-deposition of residual Mg vapor during the cooling process. This is most significant in the XRD pattern of sample 4, which was close



**Figure 2.** XRD patterns of the samples. Peaks corresponding to the Al<sub>2</sub>O<sub>3</sub> substrate are shown in this figure marked by '\*'.

to the Mg source. It can be seen that the Mg peaks increased, while most of the MgB<sub>2</sub> peaks dropped. The SEM images of the samples reconfirmed this conclusion. As a result, Mg vapor pressure is seen to play a very important role in the difference between the samples; maintaining a uniform Mg vapor pressure inside the chamber is crucial in this work. In the upper region (Sample 1), where Mg vapor is insufficient, decomposition of  $B_2H_6$  happened as  $B_2H_4 \rightarrow B \downarrow + H_2$ ; boron was deposited on the substrate directly, instead of MgB<sub>2</sub>. As the Mg vapor pressure increased in the lower region, MgB<sub>2</sub> formation dominated the deposition process. But when the Mg vapor pressure was too high (as in Sample 4), re-deposition of the saturated Mg vapor occurred on the substrate surface, contaminating the MgB2 film; in our system, controlling Mg vapor pressure proved to be the difficult part. The evaporation rate of Mg is affected by the deposition of MgB<sub>2</sub> on the surface of Mg ingots.

The SEM images of the MgB<sub>2</sub> thick films are shown in figure 3. All the samples had polycrystalline structures. It can be observed from figures 3(a)-(d) that the substrates were completely coated with dense films, while granular structures of  $\sim 10 \, \mu \mathrm{m}$  were found on top of the film. Beneath the granular structures, the films of sample 2 and 3 are more dense and solid than sample 1 as more Mg vapor was available at lower positions. The dense films under the clusters demonstrated relatively good conductivity. In the image of Sample 4, a lot of brightly-colored Mg clusters were discovered. As it was placed near the Mg source, a lot of Mg redeposition happened. These granules inevitably affected the T<sub>C</sub> measurement, with lower T<sub>C</sub> and nonzero resistance transition. Figures 3(e) and (f) showed magnified view of the top isolated clusters and the bottom of sample 3 respectively. It can be observed that both them are composed by hexagonal crystallites of about 1-2  $\mu m$  in size. The MgB<sub>2</sub> grains in figure 3(e) present as good hexagonal prisms, fitting its hexagonal crystal structure, with the (0001) and (1100) planes being the faces with slower growth rate. As the deposition was conducted on polycrystalline Al<sub>2</sub>O<sub>3</sub> substrate, no textured epitaxial growth was found. The Volmer-Weber mode growth [2, 32] of the MgB<sub>2</sub> hexagonal prisms resulted in some voids and gaps between the grains. In the isolated

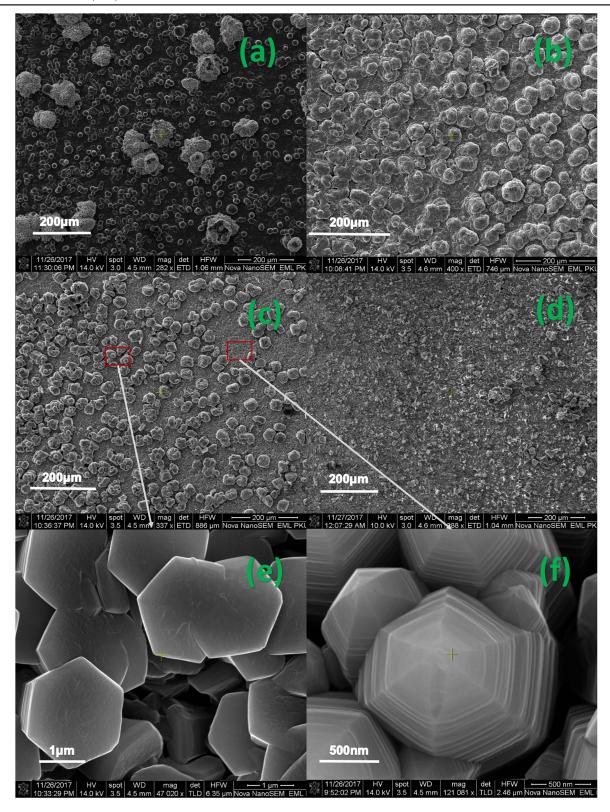
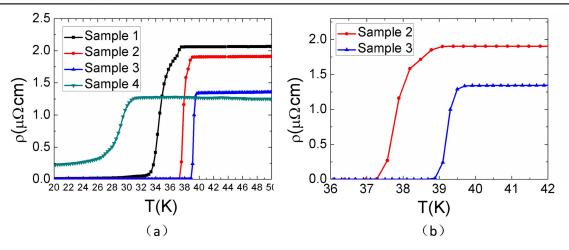


Figure 3. (a)–(d) SEM images of the four samples. (e)–(f) Magnified view of the top isolated granule and the bottom microcrystal grain of sample 3.

clusters (figure 3(f)), step-pyramid shaped grains were observed. This might indicate that the Mg vapor was depleted on the substrate surface, so that the crystal growth tended to reach out for more Mg vapor. Similarly pyramid shaped MgB<sub>2</sub> grains have been observed on Al<sub>2</sub>O<sub>3</sub> substrate by Won

et al [33]. Above all, controlling the Mg vapor pressure is the crucial controlling factor.

Figure 4 shows the temperature dependence of the resistivity of the various samples. It can be observed that all four samples exhibited a superconducting transition, while  $T_{\rm C}$ 



**Figure 4.** (a) Temperature dependence of the resistivity of the various samples. (b) Magnified view around the superconducting transition region of Samples 2 and 3.

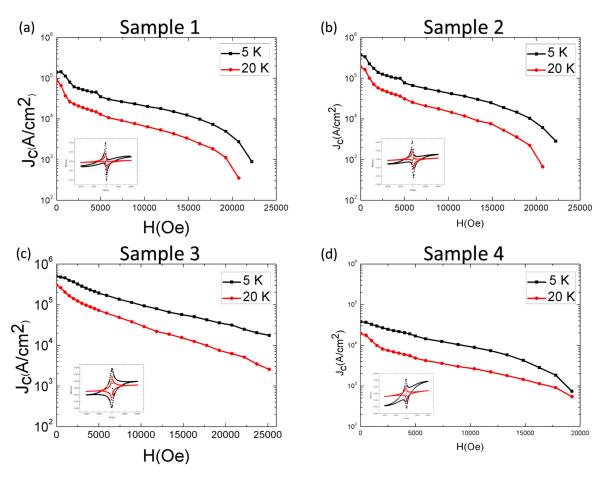


Figure 5. Magnetic field dependence of  $J_{\rm C}$  of the various samples. Insets display the respective magnetic hysteresis loops measured at 5 and 20 K.

varied with the change of position. Samples 2 and 3 respectively had onset transition temperatures of  $38.9 \, \text{K}$  and  $39.6 \, \text{K}$  with sharp transition widths of about  $0.8 \, \text{K}$  and  $0.6 \, \text{K}$ , comparable with those of high-quality planar  $MgB_2$  films fabricated on single crystal substrates by HPCVD. However, the  $T_C$  of Samples 1 and 4 was lower. Due to the insufficiency of Mg vapor, the  $T_C$  of Sample 1 decreased to  $36.8 \, \text{K}$ , and the corresponding transition width increased to  $2.5 \, \text{K}$ .

Meanwhile, Sample 4 displayed a performance reduction of the  $T_C$  to  $30.3\,K$  and  $\Delta T_C$  to  $4.2\,K,$  and a high residual resistance was measured when the superconducting transition completed. As the position was close to the Mg source, the Mg vapor around Sample 4 was the highest among four positions and a lot of Mg granules re-deposited and contaminated the film—which was also observed using the SEM. The Mg granules may cause a short-circuit between the

current and voltage probes in the four-probe method, leading to voltage pick-up. The  $\rho$ -T results indicate that we can develop high  $T_C$  MgB $_2$  films on 3D structures by HPCVD with induction heating. The area of high-quality films is sensitive to the position in vertical direction between the Mg source and the  $B_2H_6$  gas. It is also influenced by the position in the induction coil, which determines the heating/temperature distribution.

The magnetic field dependence of  $J_{\rm C}$  was calculated from the magnetization hysteresis loops using the Bean model [34]  $J_{\rm C} = 20\Delta M/[Va(1-a/3b)]$ , where  $\Delta M$  is the height difference of the M-H loop, V is the volume of film, and a, b are the sample dimensions with a < b. The  $J_C$ -H curves are shown in figure 5. The  $J_{\rm C}$  (0) at 5 K for samples 1 to 4 were  $1.4 \times 10^5$ ,  $3.8 \times 10^5$ ,  $5.1 \times 10^5$ , and  $3.8 \times 10^4 \,\mathrm{A} \cdot \mathrm{cm}^{-2}$ respectively. These  $J_{\rm C}$  values are lower than those on single crystal Al<sub>2</sub>O<sub>3</sub> or SiC substrate [17]. As is shown in figure 3, the films we obtained have a lot of voids and gaps inside, which potentially affect the current carrying capacity of the films and lead to a decrease of  $J_c$ . However, the  $J_C$  (0) values of samples 2 and 3 are close to that of MgB2 planar films fabricated on metal substrates [18, 23]. The  $J_C$  result is predictable, as the substrates we used are polycrystalline, the growth mode thus being non-epitaxial and leading to inevitable voids in the films. On the other hand, the fast deposition rate further increased the number of those voids. The comparison of the four  $J_C$ -H curves also shows that Samples 2 and 3 have better superconducting performance than Samples 1 and 4, which indicates that with specifically controlled growth conditions, an increase in  $J_{\rm C}$  could be expected. The low value  $J_{\rm C}$  for Sample 4 might be caused by the poor connection between grains in the film, which is a result of Mg contamination. In the M-H diagram (inserts in figure 5), distortion of the M-H loop has been overserved. The distortion of the loops is related to the flux pinning in the non-epitaxial MgB<sub>2</sub> films. Similar distortion can be observed in YBCO research [35, 36].

## 4. Conclusion

In this work, we studied the fabrication of MgB2 thick films by HPCVD on non-metal 3D structures, which is needed in magnetic shielding. The films were fabricated on polycrystalline Al<sub>2</sub>O<sub>3</sub> cylinders, and showed a high transition temperature of 39 K; a high deposition rate was obtained, proving the feasibility of the method. The critical current density was  $\sim 10^5 \,\mathrm{A\cdot cm}^{-2}$ , lower than that of planar MgB<sub>2</sub> films on single crystal substrate, but comparable with results on metal substrate. The lowering of  $J_{\rm C}$  is possibly due to voids and discontinuities caused by the non-epitaxial Volmer -Weber mode growth of MgB<sub>2</sub> and fast deposition rate. The size of MgB<sub>2</sub> films produced is of the order of centimeters, which is suitable for SQUID or other high resolution magnetic detectors and meets the demand of superconducting magnetic shielding. This is the first time that HPCVD MgB<sub>2</sub> films have been fabricated on 3D ceramic structures for magnetic shielding. In future experiments, the shielding effect will be tested, and further optimization of the system done to deposit higher quality  $MgB_2$  films on larger 3D structures. A  $MgB_2$  film superconducting magnetic shielding device for magnetic detectors working at a temperature of 20–40 K will be built.

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